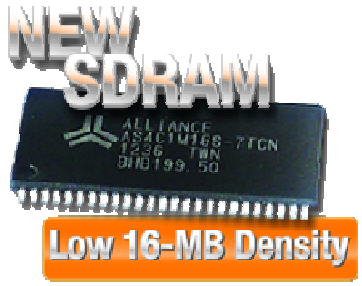
Alliance Memory's New High-Speed CMOS Synchronous DRAM with Low 16MB Density in 50-Pin TSOP II Package

Alliance Memory has introduced a new high-speed CMOS synchronous DRAM (SDRAM) with a low density of 16MB in a 50-pin, 400-mil plastic TSOP II package. The AS4C1M16S offers a fast access time from clock of 5.4 ns at a 7-ns clock cycle and a fast clock rate of 143MHz.



The new SDRAM is optimized for medical, industrial, automotive and telecom applications requiring high memory bandwidth. It is particularly well-suited to high-performance PC applications.

They are internally configured as dual banks of 512K word x 16 bits with a synchronous interface and the SDRAM operates from a single +3.3V (± 0.3 V) power supply. The AS4C1M16S is Lead (Pb) and Halogen Free.

The AS4C1M16S provides programmable read or write burst lengths of 1, 2, 4, 8 or full page; with a burst termination option. An auto pre-charge function provides a self-timed row pre-charge initiated at the end of the burst sequence. Easy-to-use refresh functions includes *auto or self-refresh*, while a programmable mode register allows the system to choose the most suitable modes to maximize performance.

Alliance Memory's legacy ICs provide reliable drop-in, pin-for-pin-compatible replacements for a number of similar solutions. The AS4C1M16S is the latest in their full line of high-speed SDRAMs which now includes devices with densities of 16MB, 64MB, 128MB and 256MB.

Datasheets and additional information can be found on www.alliancememory.com